

**METHOD FOR INTERCONNECTION BETWEEN TRANSFER DEVICES
AND STORAGE CAPACITORS IN MEMORY CELLS AND DEVICE
FORMED THEREBY**

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ABSTRACT OF THE DISCLOSURE

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The preferred embodiment of the present invention provides unique structure for connecting between a storage capacitor and a transfer device in a memory cell and a method for fabricating the same. The preferred embodiment of the present invention forms a capacitor structure having a "lip" at its top on the side the connection is to be made. To form the connection, dopant is diffused from the lower surface of the capacitor step and into the substrate, forming a surface strap to connect between the storage capacitor and the transfer device. This surface strap has the advantage of being self aligned with the storage capacitor and the transfer device, facilitating higher memory cell densities. The present invention can be used to form connections between storage capacitors and memory cells in a wide variety of devices.

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